

## Dual P-Channel MOSFET MEM2311SG Series

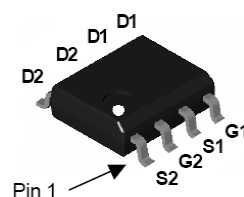
### Description:

**MEM2311SG Series** Dual P-channel enhancement mode field-effect transistor, produced with high cell density DMOS trench technology, which is especially used to minimize on-state resistance.

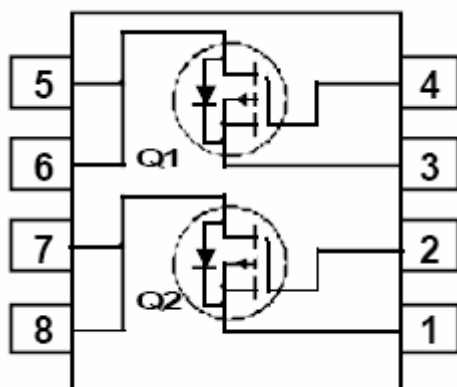
This device particularly suits low voltage applications, and low power dissipation.

### Feature:

- -30V/-6A  
 $R_{DS(ON)} = 52m\Omega @ V_{GS} = -10V, I_D = -6A$   
 $R_{DS(ON)} = 67m\Omega @ V_{GS} = -4.5V, I_D = -4A$
- High Density Cell Design For Ultra Low On-Resistance
- Surface mount package: SOP8



### Pin Configuration:



### Typical Application:

- Power management
- Load switch
- Battery protection

### Absolute Maximum Ratings:

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	$V_{DSS}$	-30V	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	$I_D$	-6	A
Total Power Dissipation	$P_d$	1	W
Operating Temperature Range	$T_{Opr}$	150	$^{\circ}C$
Storage Temperature Range	$T_{stg}$	-65/150	$^{\circ}C$

## Electrical Characteristics:

### MEM2311SG

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-34		V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1.2	-1.3	-2	V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =20V		0.8	30	nA
		V <sub>DS</sub> =0V, V <sub>GS</sub> =-20V		-0.8	-30	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V V <sub>GS</sub> =0V		-3.5	-300	nA
Static Drain-Source On-Resistance	R <sub>DS(ON)1</sub>	V <sub>GS</sub> =-10V,I <sub>D</sub> =-6A	33	52	65	mΩ
	R <sub>DS(ON)2</sub>	V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-4A	50	67	80	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -5 V,I <sub>D</sub> = -5 A		10		S
Drain-Source Diode Forward Current	I <sub>S</sub>				-1.3	A
Source-drain (diode forward) voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =-1A		-0.8	-1.2	V
Dynamic Characteristics						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0 V, f = 1 MHz		530		pF
Output Capacitance	C <sub>oss</sub>			140		
Reverse Transfer Capacitance	C <sub>rss</sub>			70		
Switching Characteristics						
Turn-On Delay Time	td(on)	V <sub>DD</sub> = -15 V, I <sub>D</sub> =-1 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 6 Ω		8	15	ns
Rise Time	tr			15	25	
Turn-Off Delay Time	td(off)			15	25	
Fall-Time	tf			10	17	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -5V, I <sub>D</sub> = -5A		10	15	nC
Gate-Source Charge	Q <sub>gs</sub>			2.2		
Gate-Drain Charge	Q <sub>gd</sub>			2		

## Typical Performance Characteristics:

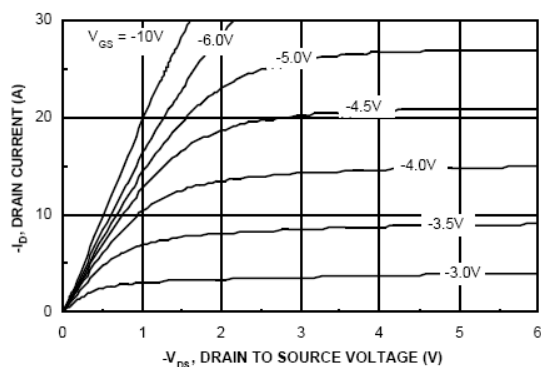


Figure 1. On-Region Characteristics.

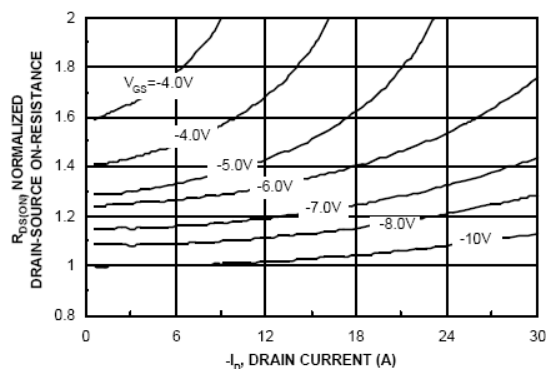


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

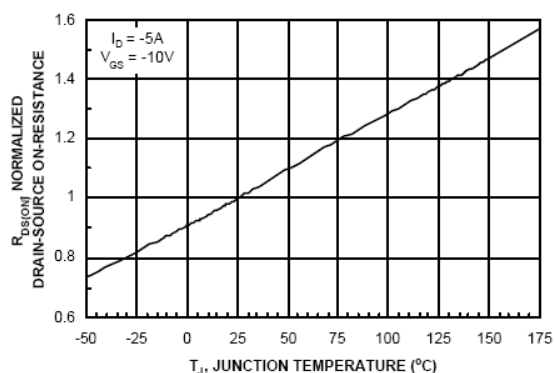


Figure 3. On-Resistance Variation with Temperature.

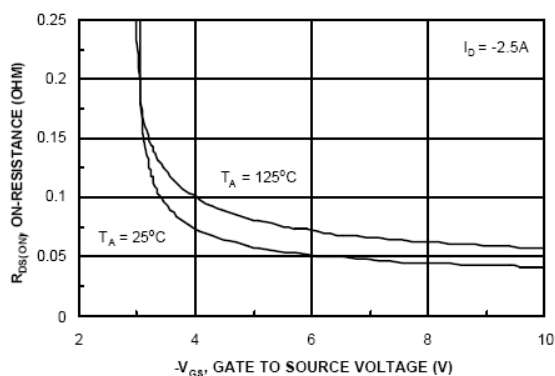


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

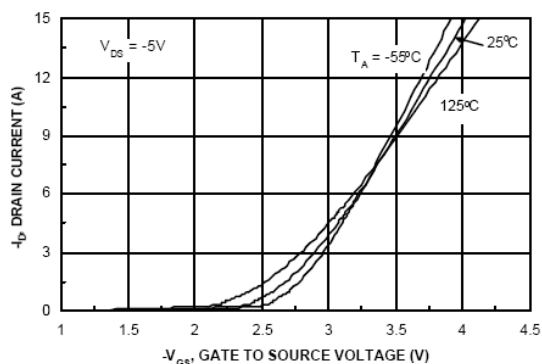


Figure 5. Transfer Characteristics.

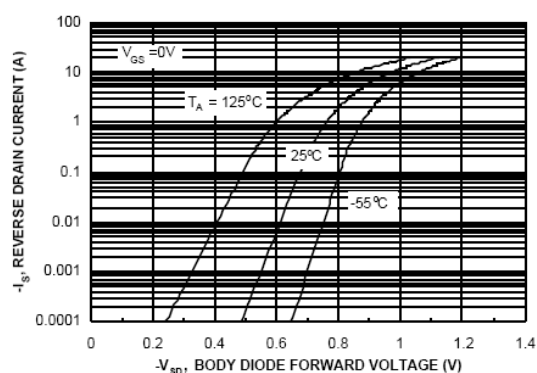


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

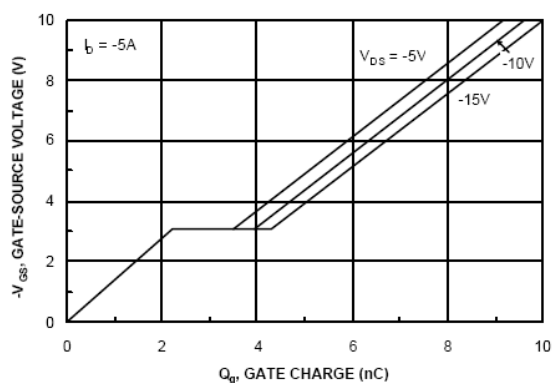


Figure 7. Gate Charge Characteristics.

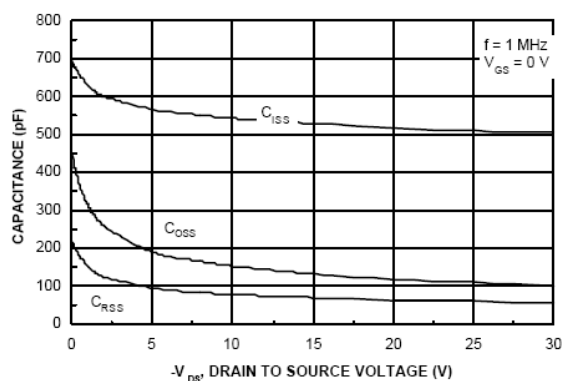


Figure 8. Capacitance Characteristics.

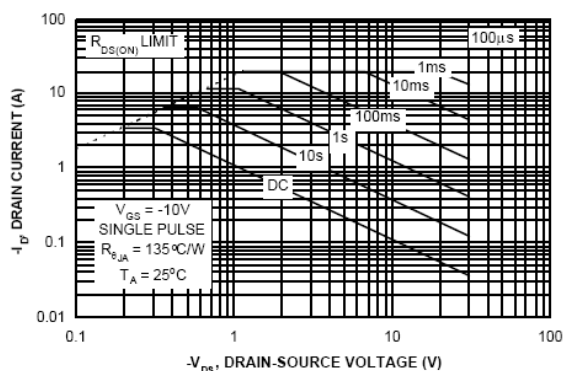


Figure 9. Maximum Safe Operating Area.

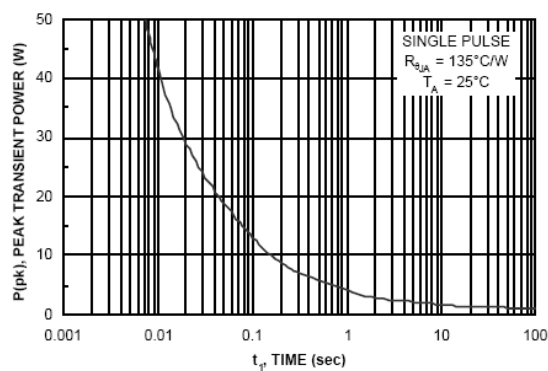


Figure 10. Single Pulse Maximum Power Dissipation.

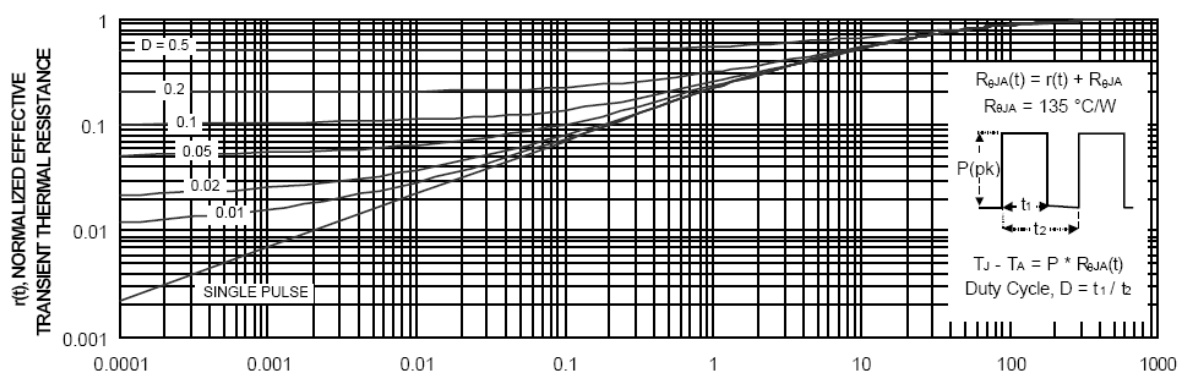
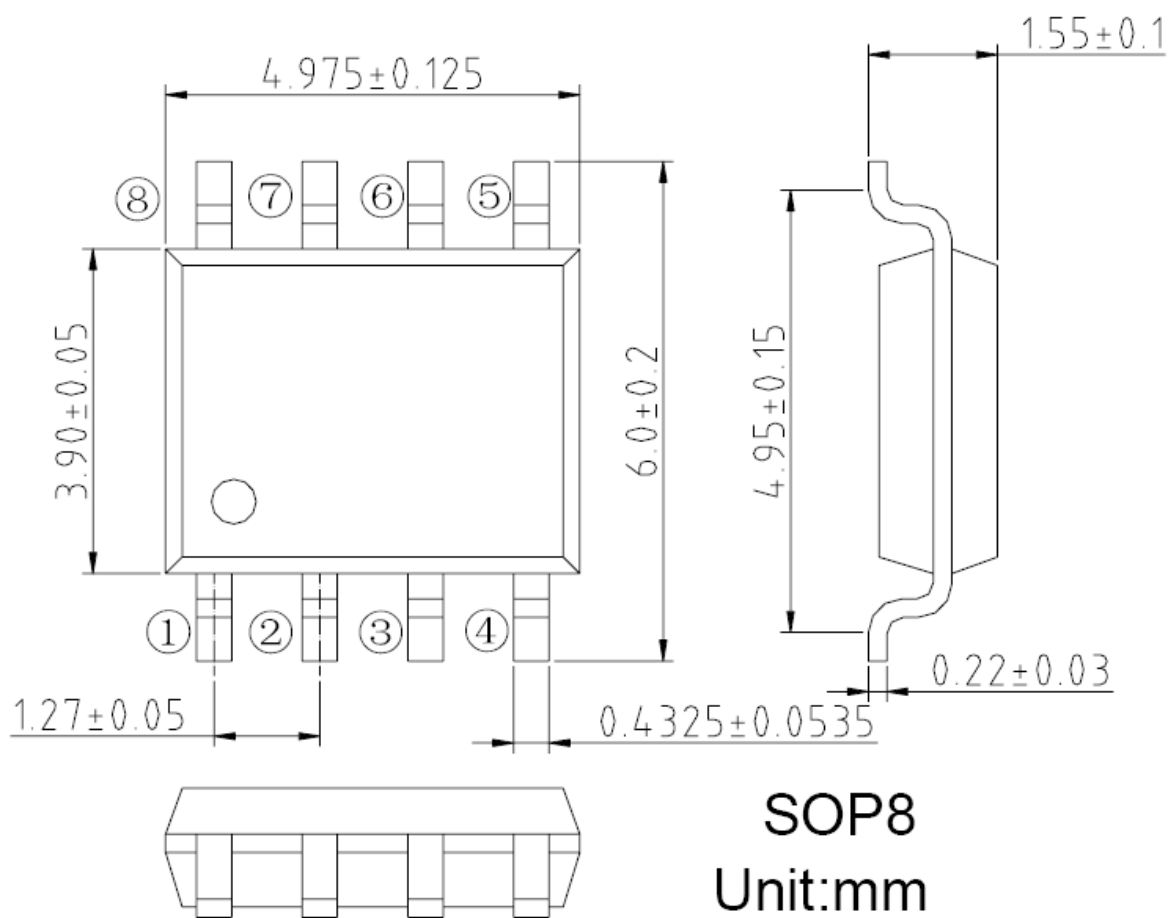


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.  
Transient thermal response will change depending on the circuit board design.

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